



TM05P04I

P-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

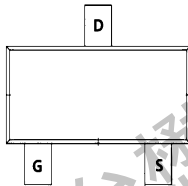
$V_{DS} = -40V, I_D = -4.8A$

$R_{DS(ON)} = 47m\Omega$ (Typ.) @ $V_{GS} = -10V$

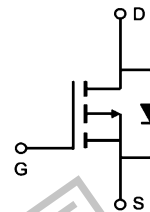
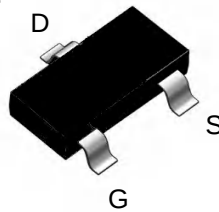
100% UIS Tested
100% R_g Tested



I: SOT-23



Marking: 5P04



Absolute Maximum Ratings $T_A = 25^\circ C$ un (less otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current	-4.8	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current	-3.6	A
I_{DM}	Pulsed Drain Current ²	-22	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ³	2.0	W
$P_D @ T_A = 70^\circ C$	Total Power Dissipation ³	1.5	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	65	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ ($t \leq 10s$)	---	48	$^\circ C/W$

TM05P04I
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Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -40V, V _{GS} =0V	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.4	-1.75	-2.0	V
R _{DS(on)}	Static Drain-Source on-Resistance Note2	V _{GS} = -10V, I _D = -5A	-	47	52	mΩ
		V _{GS} = -4.5V, I _D = -4A	-	53	69	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -20V, V _{GS} =0V, f=1.0MHz	-	869	-	pF
C _{oss}	Output Capacitance		-	94	-	pF
C _{rss}	Reverse Transfer Capacitance		-	69	-	pF
Q _g	Total Gate Charge	V _{DS} = -20V, I _D = -4A, V _{GS} = -10V	-	17.3	-	nC
Q _{gs}	Gate-Source Charge		-	3.2	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	4.3	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} = -20V, I _D = -4A, V _{GS} = -10V, R _{GEN} =3Ω	-	10.3	-	ns
t _r	Turn-on Rise Time		-	4.3	-	ns
t _{d(off)}	Turn-off Delay Time		-	39	-	ns
t _f	Turn-off Fall Time		-	46.5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	- 4.8	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-22	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -5.5A	-	-0.8	-1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S = -5.5A,	-	17	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs	-	11.5	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

 2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

TM05P04I

P-Channel Enhancement Mosfet

Typical Performance Characteristics

Figure1: Output Characteristics

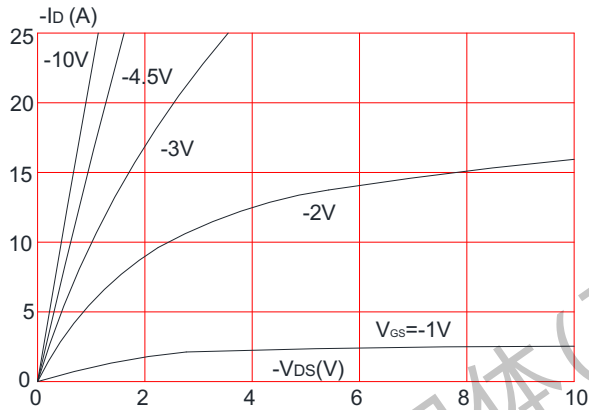


Figure 2: Typical Transfer Characteristics

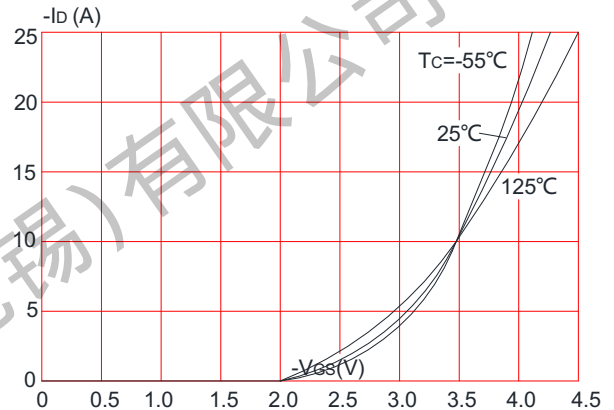


Figure 3: On-resistance vs. Drain Current

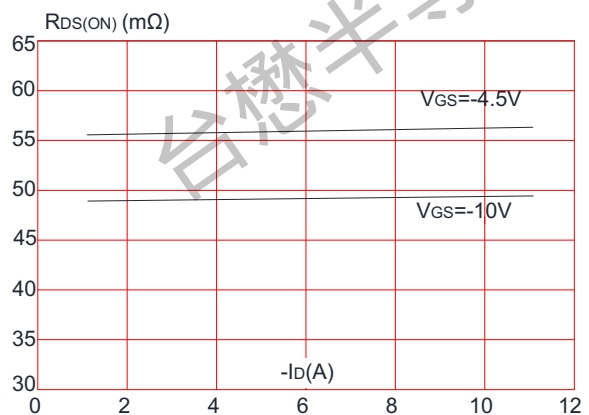


Figure 4: Body Diode Characteristics

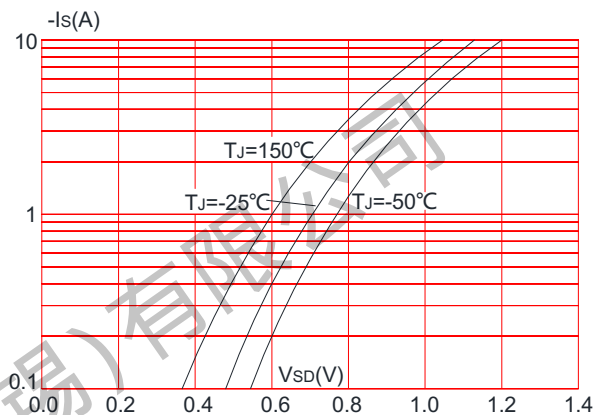


Figure 5: Gate Charge Characteristics

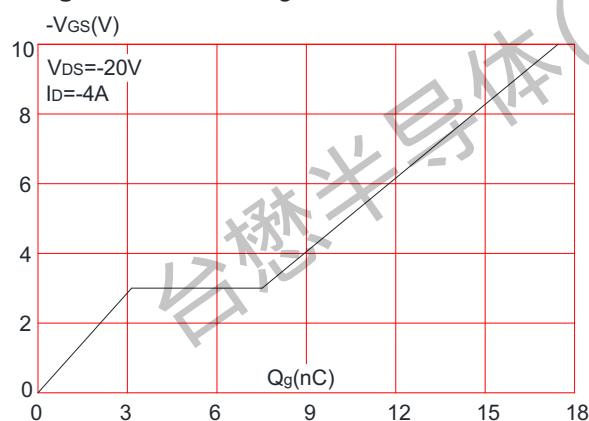
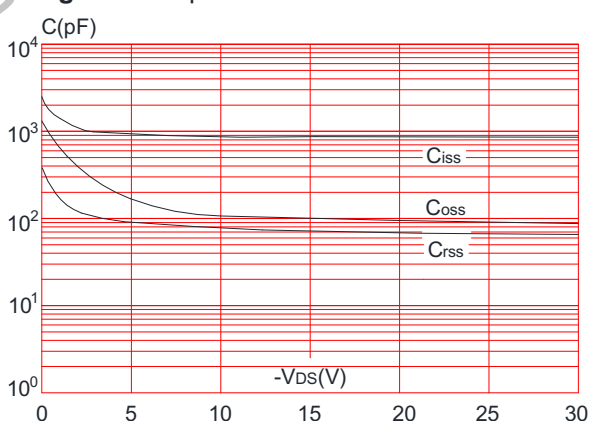


Figure 6: Capacitance Characteristics



TM05P04I

P-Channel Enhancement Mosfet

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

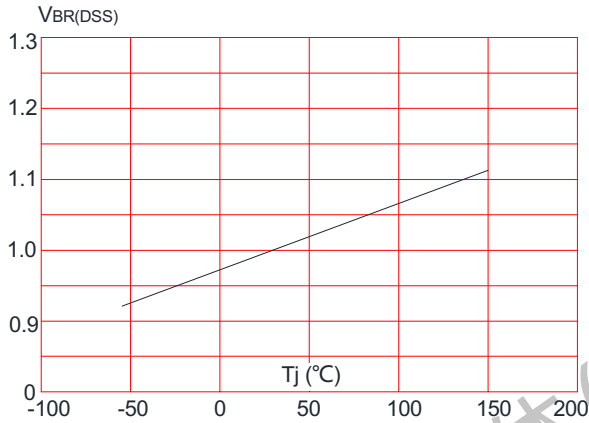


Figure 8: Normalized on Resistance vs. Junction Temperature

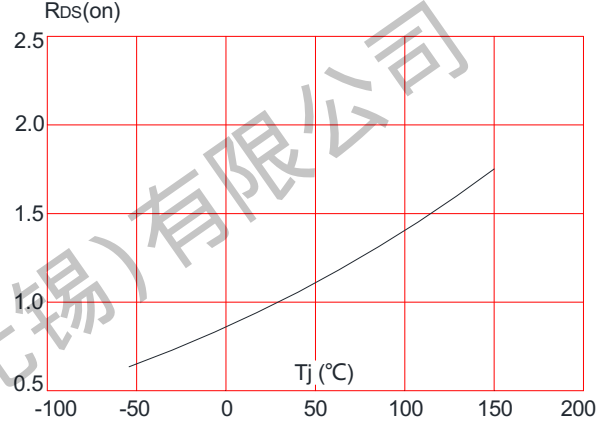


Figure 9: Maximum Safe Operating Area

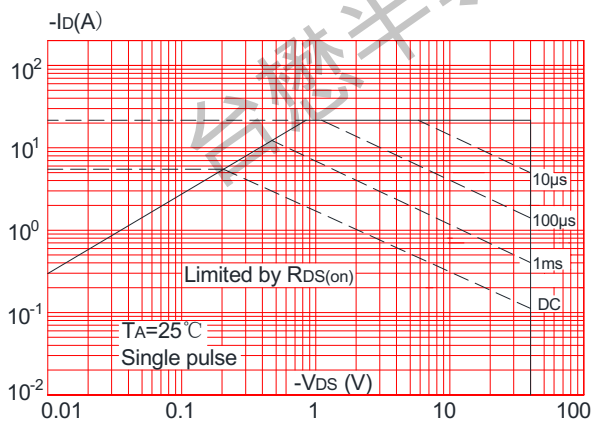


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

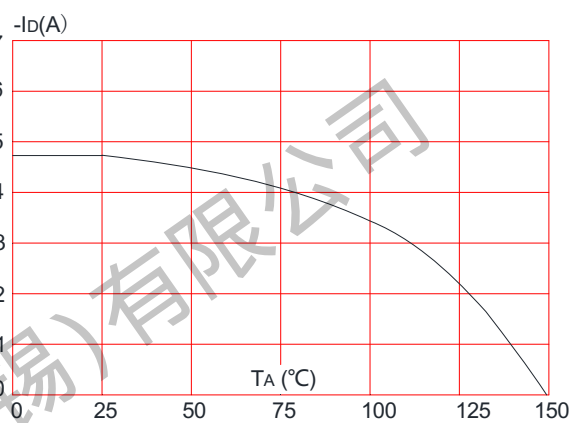
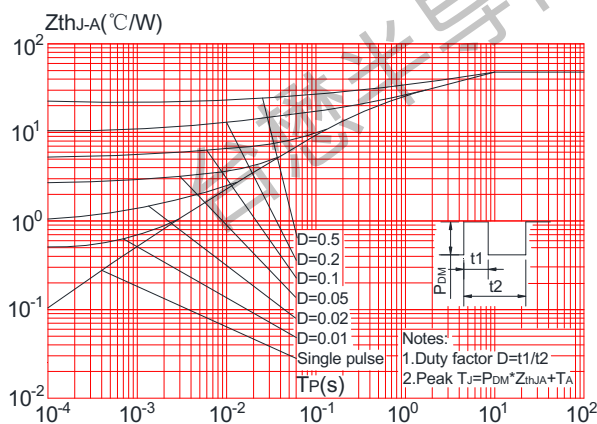


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

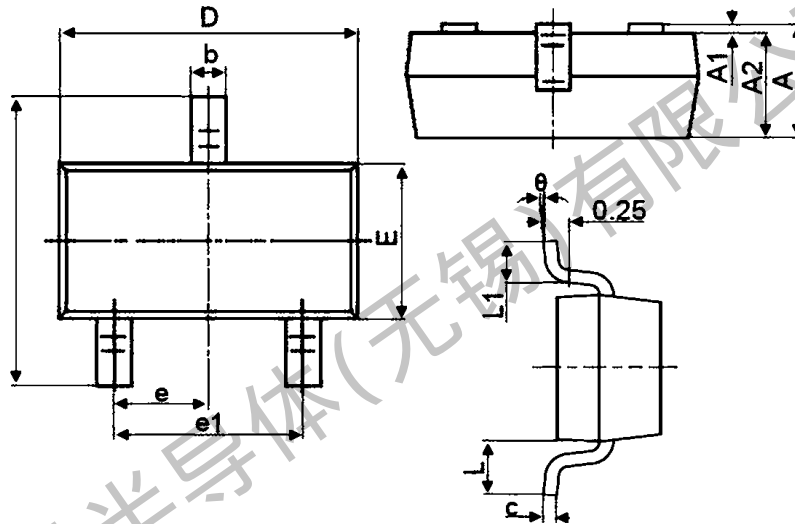




TM05P04I

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Package Mechanical Data:SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

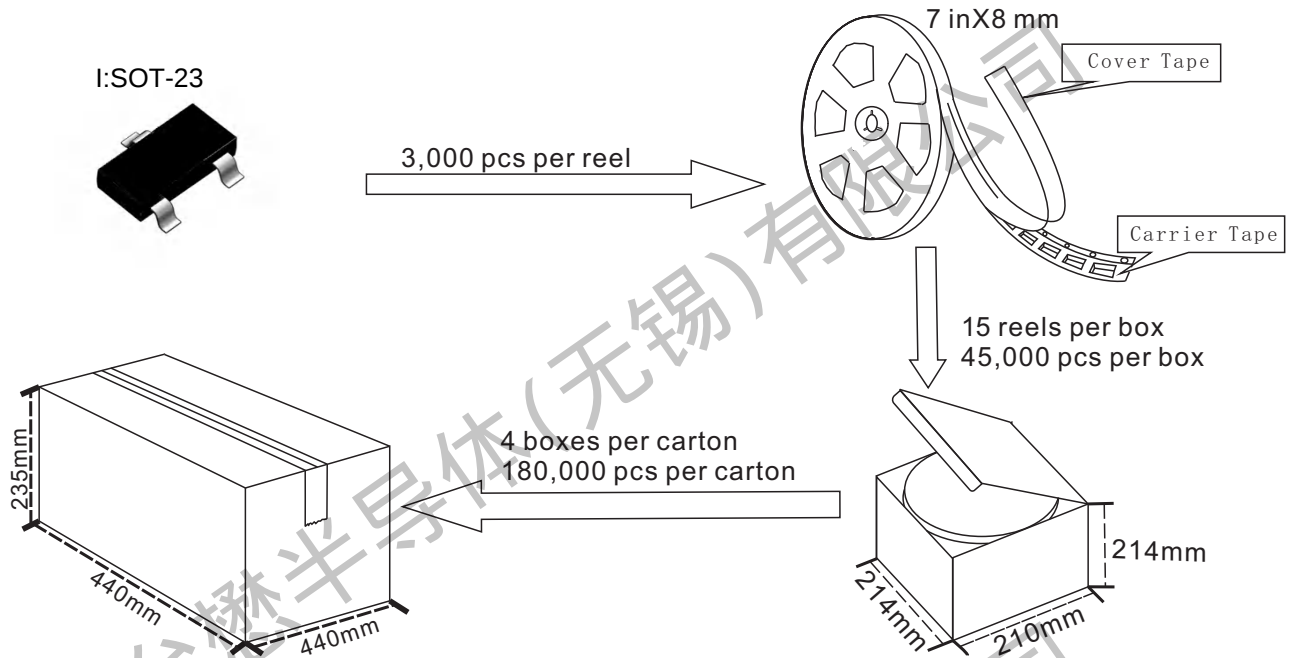


TM05P04I

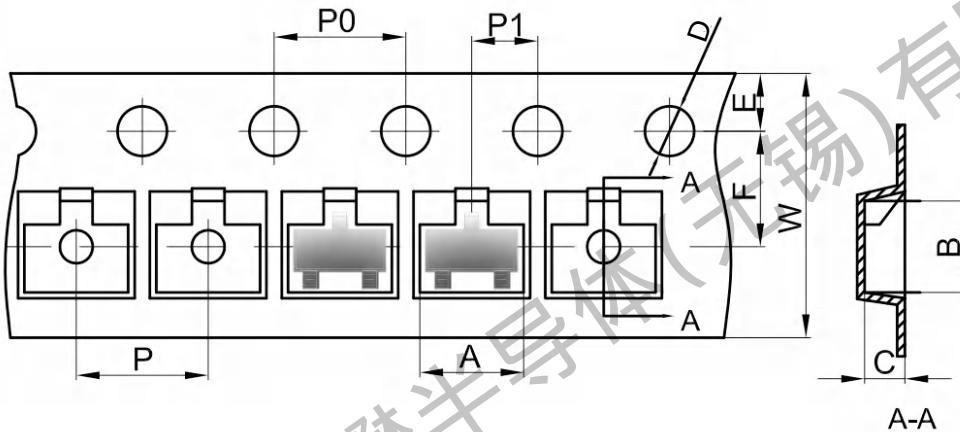
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SOT-23 Packing

1. The method of packaging and dimension are shown as below figure. (Dimension in mm)



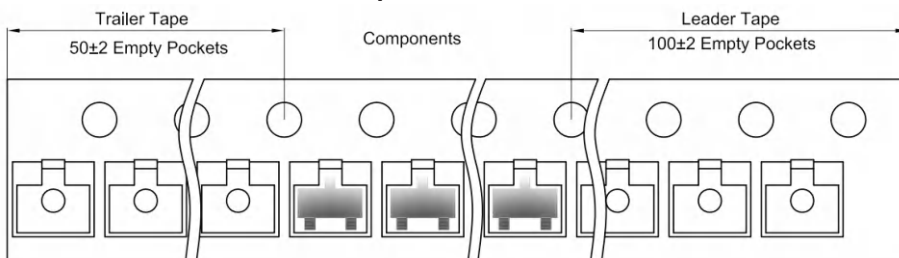
SOT-23 Embossed Carrier Tape



Dimensions are in millimeter

Pkg type	A	B	C	D	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



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Revision history:

Date	Rev	Description	Page
2023.08.11	23.08	Original	